

Femtowatt Photoreceiver with InGaAs PIN Photodiode



The photoreceiver will be delivered without post holder and post.

<p>Features</p>	<ul style="list-style-type: none"> • InGaAs PIN photodiode, 0.5 mm active diameter • Ultra low noise, NEP 7.5 fW/√Hz • Amplifier transimpedance gain 1×10^{11} V/A • Max. conversion gain 0.95×10^{11} V/W @ 1550 nm • Wavelength range 900 ... 1700 nm 																											
<p>Applications</p>	<ul style="list-style-type: none"> • Fluorescence measurements • NIR spectroscopy • Electrophoresis • Replacement for (liquid nitrogen) cooled Ge photodiodes and avalanche photodiodes (APDs) 																											
<p>Specifications</p>	<table border="0"> <tr> <td>Test conditions</td> <td colspan="2">$V_s = \pm 15$ V, $T_A = 25^\circ\text{C}$ Warm-up 20 minutes (min. 10 minutes recommended)</td> </tr> <tr> <td rowspan="2">Gain</td> <td>Amplifier transimpedance</td> <td>1.0×10^{11} V/A (@ ≥ 100 kΩ load)</td> </tr> <tr> <td>Max. conversion gain</td> <td>0.95×10^{11} V/W (@ 1550 nm)</td> </tr> <tr> <td rowspan="3">Frequency Response</td> <td>Lower cut-off frequency</td> <td>DC</td> </tr> <tr> <td>Upper cut-off frequency (-3 dB)</td> <td>20 Hz (± 20 %)</td> </tr> <tr> <td>Rise/fall time (10 % - 90 %)</td> <td>18 ms (± 20 %)</td> </tr> <tr> <td rowspan="3">Detector</td> <td>Detector material</td> <td>InGaAs PIN photodiode</td> </tr> <tr> <td>Active area</td> <td>\varnothing 0.5 mm</td> </tr> <tr> <td>Spectral response</td> <td>900 ... 1700 nm</td> </tr> <tr> <td rowspan="2">Input</td> <td>Optical saturation power</td> <td>110 pW (for linear amplification, @ 1550 nm)</td> </tr> <tr> <td>NEP</td> <td>7.5 fW/√Hz (@ 1550 nm, 1 Hz)</td> </tr> </table>	Test conditions	$V_s = \pm 15$ V, $T_A = 25^\circ\text{C}$ Warm-up 20 minutes (min. 10 minutes recommended)		Gain	Amplifier transimpedance	1.0×10^{11} V/A (@ ≥ 100 k Ω load)	Max. conversion gain	0.95×10^{11} V/W (@ 1550 nm)	Frequency Response	Lower cut-off frequency	DC	Upper cut-off frequency (-3 dB)	20 Hz (± 20 %)	Rise/fall time (10 % - 90 %)	18 ms (± 20 %)	Detector	Detector material	InGaAs PIN photodiode	Active area	\varnothing 0.5 mm	Spectral response	900 ... 1700 nm	Input	Optical saturation power	110 pW (for linear amplification, @ 1550 nm)	NEP	7.5 fW/√Hz (@ 1550 nm, 1 Hz)
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Specifications (continued)	
Output	Output voltage range ± 10 V (@ ≥ 100 k Ω load) Output impedance 50 Ω (designed for ≥ 100 k Ω load) Offset voltage 0 V, adjustable by offset potentiometer within ± 1.6 V Max. output current ± 25 mA Output noise ca. 20 mV _{pp} or 3 mV _{RMS} (@ ≥ 100 k Ω load, no signal on detector)
Power Supply	Supply voltage ± 15 V Supply current ± 15 mA typ. (depends on operating conditions, recommended power supply capability min. ± 50 mA)
Case	Weight 190 g (0.42 lbs) Material AlMg3/4.5Mn, nickel-plated
Temperature Range	Storage temperature -40 ... +100 °C Operating temperature 0 ... +60 °C

Absolute Maximum Ratings	Optical input power 10 mW Power supply voltage ± 22 V
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